

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1015(L)

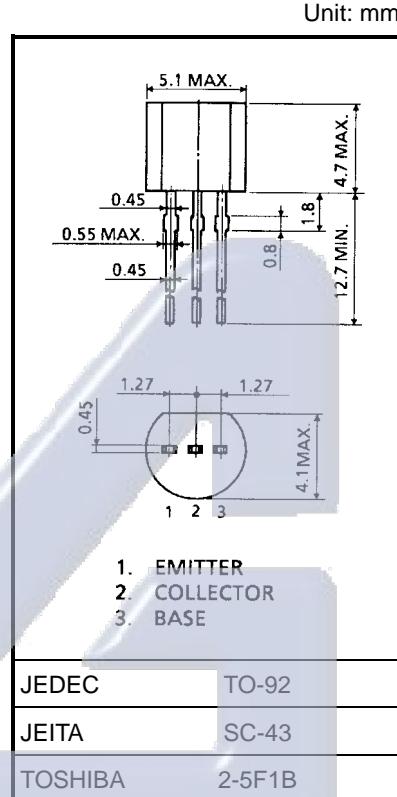
Audio Frequency Amplifier Applications

Low Noise Amplifier Applications

- High voltage and high current: $V_{CEO} = -50$ V (min), $I_C = -150$ mA (max)
- Excellent hFE linearity: $hFE(2) = 80$ (typ.) at $V_{CE} = -6$ V, $I_C = -150$ mA
: $hFE(I_C = -0.1$ mA)/ $hFE(I_C = -2$ mA) = 0.95 (typ.)
- Low noise: $NF = 0.2$ dB (typ.) ($f = 1$ kHz)
- Complementary to 2SC1815 (L)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-150	mA
Base current	I_B	-50	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C

**Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -50$ V, $I_E = 0$	—	—	-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5$ V, $I_C = 0$	—	—	-0.1	μA
DC current gain	$h_{FE}(1)$ (Note)	$V_{CE} = -6$ V, $I_C = -2$ mA	70	—	400	
	$h_{FE}(2)$	$V_{CE} = -6$ V, $I_C = -150$ mA	25	80	—	
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -100$ mA, $I_B = -10$ mA	—	-0.1	-0.3	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = -100$ mA, $I_B = -10$ mA	—	—	-1.1	V
Transition frequency	f_T	$V_{CE} = -10$ V, $I_C = -1$ mA	80	—	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$ $f = 1$ MHz	—	4	7	pF
Base intrinsic resistance	$r_{bb'}$	$V_{CB} = -10$ V, $I_E = 1$ mA $f = 30$ MHz	—	30	—	Ω
Noise figure	NF (1)	$V_{CE} = -6$ V, $I_C = -0.1$ mA $f = 100$ Hz, $R_G = 10$ kΩ	—	0.5	6	dB
	NF (2)	$V_{CE} = -6$ V, $I_C = -0.1$ mA $f = 1$ kHz, $R_G = 10$ kΩ	—	0.2	3	

Note: hFE (1) classification O: 70~140, Y: 120~240, GR: 200~400

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